

In the Claims:

Claim 1 (currently amended): A circuit comprising:

a bipolar transistor having a base, an emitter, and a collector, said bipolar transistor comprising a SiGe HBT;

a field effect transistor having a gate, a source, and a drain;

said base of said bipolar transistor being an input of said circuit;

said emitter of said bipolar transistor being coupled to a first reference voltage;

said collector of said bipolar transistor being coupled to said source of said field effect transistor;

said gate of said field effect transistor being coupled to a bias voltage;

said drain of said field effect transistor being coupled to a second reference voltage;

said drain of said field effect transistor being an output of said circuit, ~~and;~~

wherein said drain of said field effect transistor is not coupled to said base of said

bipolar transistor by a feedback network, wherein said drain of said field effect

transistor is directly coupled to a BiFET low noise amplifier output by a first

capacitor.

Claim 2 (original): The circuit of claim 1 wherein said emitter of said bipolar transistor is coupled to said first reference voltage through a first impedance circuit.

Claim 3 (original): The circuit of claim 2 wherein said first impedance circuit comprises an inductor.

Claim 4 (original): The circuit of claim 1 wherein said drain of said field effect transistor is coupled to said second reference voltage through a second impedance circuit.

Claim 5 (currently amended): The circuit of claim 4 wherein said second impedance circuit comprises an inductor and a said first capacitor.

Claim 6 (original): The circuit of claim 1 wherein said bipolar transistor is an NPN SiGe HBT.

Claim 7 (original): The circuit of claim 1 wherein said field effect transistor is an NFET.

Claim 8 (original): The circuit of claim 1 wherein said bipolar transistor is coupled to said field effect transistor in a cascode configuration in a BiFET low noise amplifier.

Claim 9 (original): The circuit of claim 1 wherein said first reference voltage is a ground voltage.

Claim 10 (canceled).

Claim 11 (original): The circuit of claim 5 wherein said inductor couples said drain of said field effect transistor to said second reference voltage.

Claim 12 (currently amended): The circuit of claim 1 wherein a second capacitor couples a received RF signal to said input of said circuit.

Claim 13 (original): The circuit of claim 1 wherein said second reference voltage is Vdd.

Claim 14 (currently amended): A BiFET low noise amplifier comprising:
a bipolar transistor having a base, an emitter, and a collector, said bipolar transistor comprising a SiGe HBT;
a field effect transistor having a gate, a source, and a drain;
an input of said BiFET low noise amplifier being coupled to said base of said bipolar transistor;

said emitter of said bipolar transistor being coupled to a first reference voltage through a first impedance circuit;

said collector of said bipolar transistor being coupled to said source of said field effect transistor;

said gate of said field effect transistor being coupled to a bias voltage;

said drain of said field effect transistor being coupled to a second reference voltage through a second impedance circuit, said drain of said field effect transistor being directly coupled to an output of said BiFET low noise amplifier by a first capacitor, and wherein said drain of said field effect transistor is not coupled to said base of said bipolar transistor by a feedback network.

Claim 15 (original): The BiFET low noise amplifier of claim 14 wherein said bipolar transistor is an NPN SiGe HBT.

Claim 16 (original): The BiFET low noise amplifier of claim 14 wherein said field effect transistor is an NFET.

Claim 17 (original): The BiFET low noise amplifier of claim 14 wherein said first reference voltage is a ground voltage.

Claim 18 (original): The BiFET low noise amplifier of claim 14 wherein said first impedance circuit comprises an inductor.

Claim 19 (currently amended): The BiFET low noise amplifier of claim 14 wherein said second impedance circuit comprises an inductor and a said first capacitor.

Claim 20 (canceled).

Claim 21 (original): The BiFET low noise amplifier of claim 19 wherein said inductor couples said drain of said field effect transistor to said second reference voltage.

Claim 22 (canceled).

Claim 23 (currently amended): The BiFET low noise amplifier of claim 14 wherein a second capacitor couples said input of said BiFET low noise amplifier to said base of said bipolar transistor.

Claim 24 (original): The BiFET low noise amplifier of claim 14 wherein a received RF signal at said input of said BiFET low noise amplifier is coupled to said base of said bipolar transistor.

Claim 25 (new): A circuit comprising:

a bipolar transistor having a base, an emitter, and a collector, said bipolar transistor comprising a SiGe HBT;

a field effect transistor having a gate, a source, and a drain;

said base of said bipolar transistor being an input of said circuit;

said emitter of said bipolar transistor being coupled to a first reference voltage through a first impedance circuit, said first impedance circuit comprising an inductor;

said collector of said bipolar transistor being coupled to said source of said field effect transistor;

said gate of said field effect transistor being coupled to a bias voltage;

said drain of said field effect transistor being coupled to a second reference voltage;

said drain of said field effect transistor being an output of said circuit, and

wherein said drain of said field effect transistor is not coupled to said base of said bipolar transistor by a feedback network.

Claim 26 (new): A BiFET low noise amplifier comprising:

a bipolar transistor having a base, an emitter, and a collector, said bipolar transistor comprising a SiGe HBT;

a field effect transistor having a gate, a source, and a drain;

an input of said BiFET low noise amplifier being coupled to said base of said bipolar transistor;

said emitter of said bipolar transistor being coupled to a first reference voltage through a first impedance circuit, said first impedance circuit comprising an inductor;

said collector of said bipolar transistor being coupled to said source of said field effect transistor;

said gate of said field effect transistor being coupled to a bias voltage;

said drain of said field effect transistor being coupled to a second reference voltage through a second impedance circuit, said drain of said field effect transistor being coupled to an output of said BiFET low noise amplifier, and wherein said drain of said field effect transistor is not coupled to said base of said bipolar transistor by a feedback network.